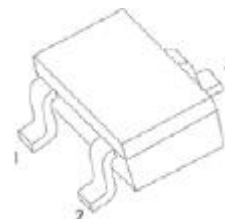


Plastic-Encapsulate MOSFETS

P-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-20V	520 mΩ@-4.5V	-0.66A
	700mΩ@-2.5V	
	950 mΩ(TYP)@-1.8V	

SOT-523



1. GATE
2. SOURCE
3. DRAIN

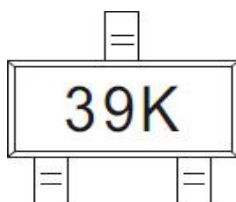
FEATURE

- Lead Free Product is Acquired
- Surface Mount Package
- P-Channel Switch with Low $R_{DS(on)}$
- Operated at Low Logic Level Gate Drive

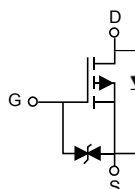
APPLICATION

- Load/Power Switching
- Interfacing, Logic Switching
- Battery Management for Ultra Small Portable Electronics

MARKING



Equivalent Circuit



Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Typical Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current (note 1)	I_D	-0.66	A
Pulsed Drain Current ($t_p=10 \mu s$)	I_{DM}	-1.2	A
Power Dissipation (note 1)	P_D	150	mW
Thermal Resistance from Junction to Ambient (note 1)	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^\circ\text{C}$
Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25\text{ }^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =-250μA	-20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =-20V,V _{GS} = 0V			-1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±10V, V _{DS} = 0V			±20	μA
Gate threshold voltage (note 2)	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.35		-1.1	V
Drain-source on-resistance (note 2)	R _{DS(on)}	V _{GS} =-4.5V, I _D =-1A			520	mΩ
		V _{GS} =-2.5V, I _D =-0.8A			700	mΩ
		V _{GS} =-1.8V, I _D =-0.5A		950		mΩ
Forward transconductance (note 2)	g _{FS}	V _{DS} =-10V, I _D =-0.54A		1.2		S
Diode forward voltage	V _{SD}	I _S =-0.5A, V _{GS} = 0V			-1.2	V
DYNAMIC CHARACTERISTICS (note 4)						
Input capacitance	C _{iSS}	V _{DS} =-16V,V _{GS} =0V,f =1MHz		113	170	pF
Output capacitance	C _{oSS}			15	25	pF
Reverse transfer capacitance	C _{rSS}			9	15	pF
SWITCHING CHARACTERISTICS (note 4)						
Turn-on delay time (note 3)	t _{d(on)}	V _{GS} =-4.5V,V _{DS} =-10V, I _D =-200mA,R _{GEN} =10Ω		9		ns
Turn-on rise time (note 3)	t _r			5.8		ns
Turn-off delay time (note3)	t _{d(off)}			32.7		ns
Turn-off fall time (note 3)	t _f			20.3		ns

Notes :

1. Surface mounted on FR4 board using the minimum recommended pad size.
2. Pulse Test : Pulse Width=300 μs , Duty Cycle=2%.
3. Switching characteristics are independent of operating junction temperatures.
4. Guaranteed by design, not subject to producing.

Typical Characteristics

